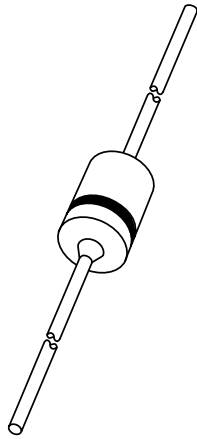


# DATA SHEET



## **1N4148; 1N4448** High-speed diodes

Product specification  
Supersedes data of 1999 May 25

2002 Jan 23

# High-speed diodes

# 1N4148; 1N4448

## FEATURES

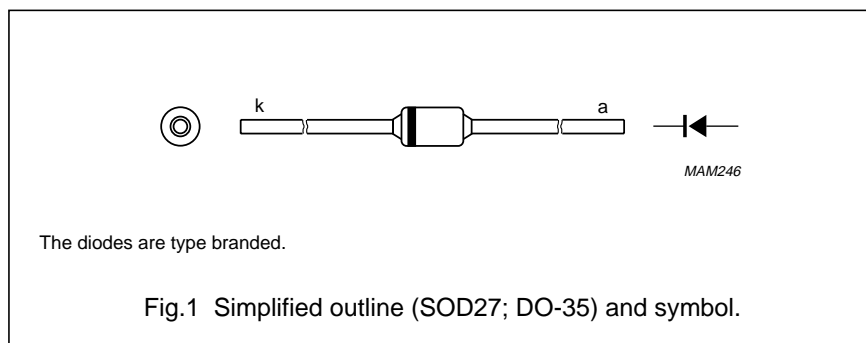
- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- General application
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

## APPLICATIONS

- High-speed switching.

## DESCRIPTION

The 1N4148 and 1N4448 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RRM}$	repetitive peak reverse voltage		–	100	V
$V_R$	continuous reverse voltage		–	75	V
$I_F$	continuous forward current	see Fig.2; note 1	–	200	mA
$I_{FRM}$	repetitive peak forward current		–	450	mA
$I_{FSM}$	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4 $t = 1\ \mu\text{s}$ $t = 1\ \text{ms}$ $t = 1\ \text{s}$	–	4 1 0.5	A A A
$P_{tot}$	total power dissipation	$T_{amb} = 25\text{ °C}$ ; note 1	–	500	mW
$T_{stg}$	storage temperature		–65	+200	°C
$T_j$	junction temperature		–	200	°C

## Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

## High-speed diodes

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**ELECTRICAL CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_F$	forward voltage 1N4148 1N4448	see Fig.3 $I_F = 10\text{ mA}$	–	1	V
		$I_F = 5\text{ mA}$	0.62	0.72	V
		$I_F = 100\text{ mA}$	–	1	V
$I_R$	reverse current	$V_R = 20\text{ V}$ ; see Fig.5		25	nA
		$V_R = 20\text{ V}$ ; $T_j = 150\text{ °C}$ ; see Fig.5	–	50	$\mu\text{A}$
$I_R$	reverse current; 1N4448	$V_R = 20\text{ V}$ ; $T_j = 100\text{ °C}$ ; see Fig.5	–	3	$\mu\text{A}$
$C_d$	diode capacitance	$f = 1\text{ MHz}$ ; $V_R = 0$ ; see Fig.6	–	4	pF
$t_{rr}$	reverse recovery time	when switched from $I_F = 10\text{ mA}$ to $I_R = 60\text{ mA}$ ; $R_L = 100\ \Omega$ ; measured at $I_R = 1\text{ mA}$ ; see Fig.7	–	4	ns
$V_{fr}$	forward recovery voltage	when switched from $I_F = 50\text{ mA}$ ; $t_r = 20\text{ ns}$ ; see Fig.8	–	2.5	V

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	lead length 10 mm; note 1	350	K/W

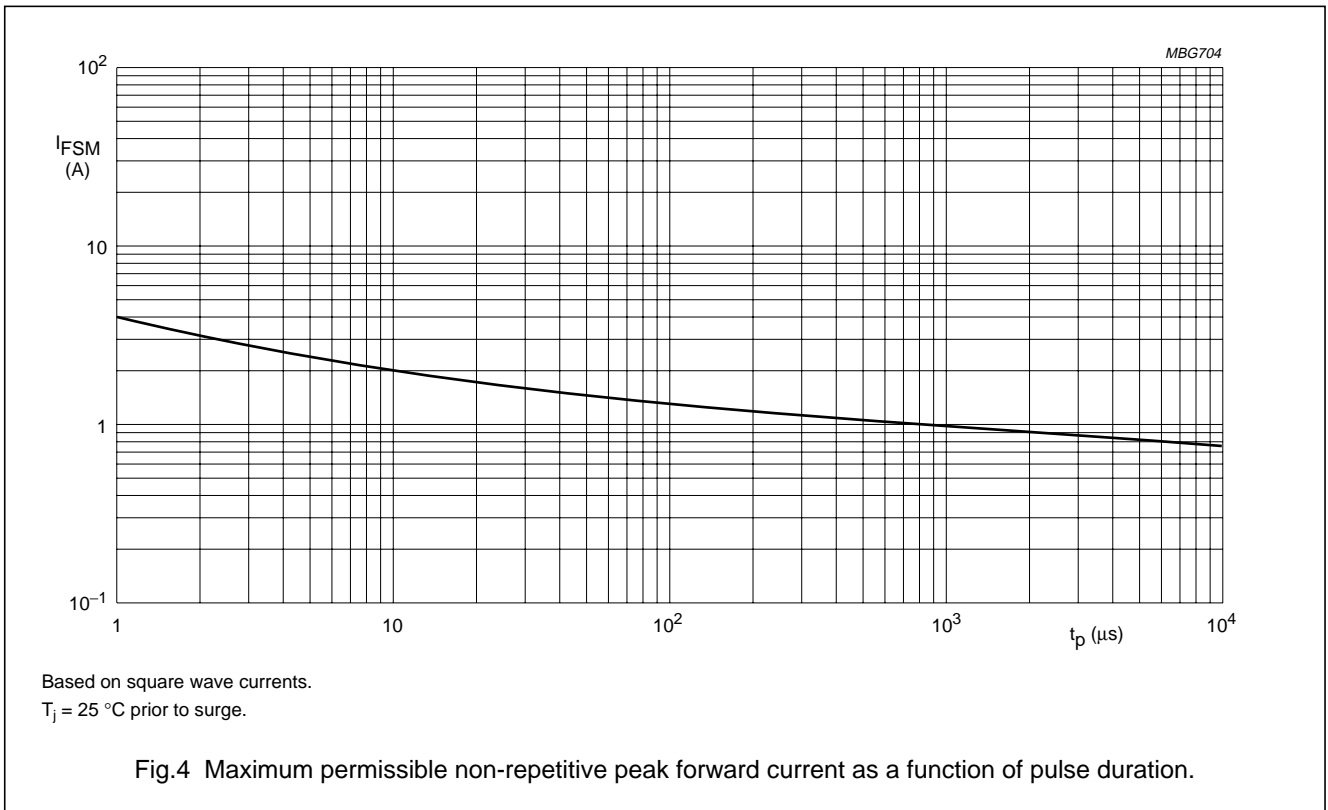
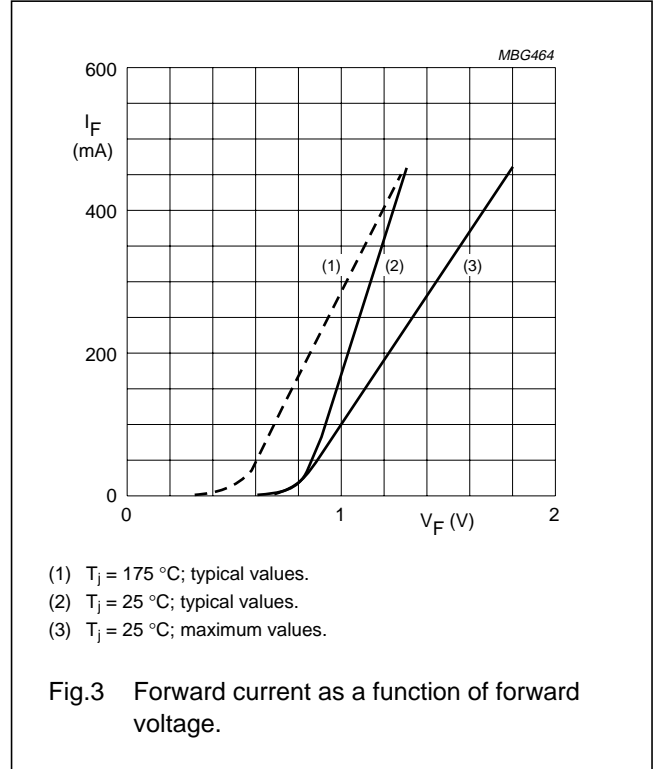
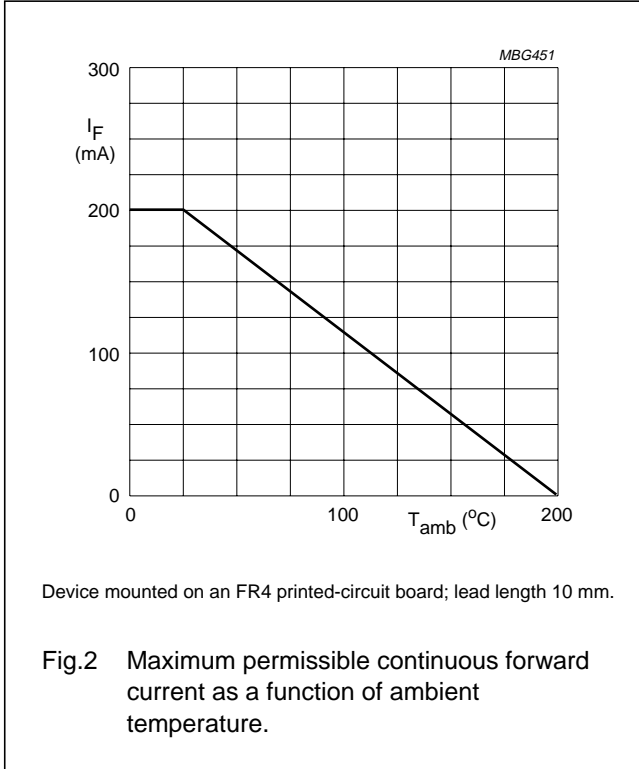
**Note**

1. Device mounted on a printed circuit-board without metallization pad.

High-speed diodes

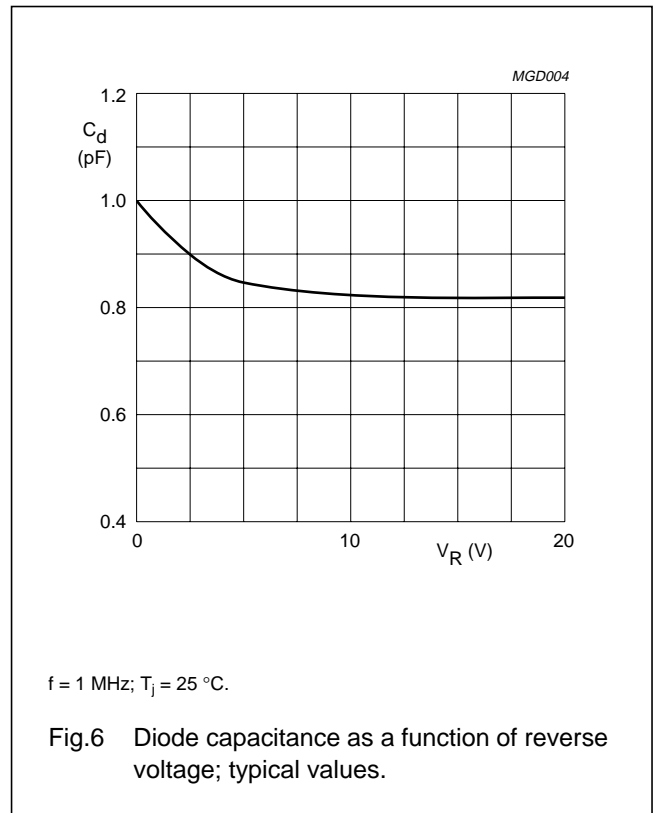
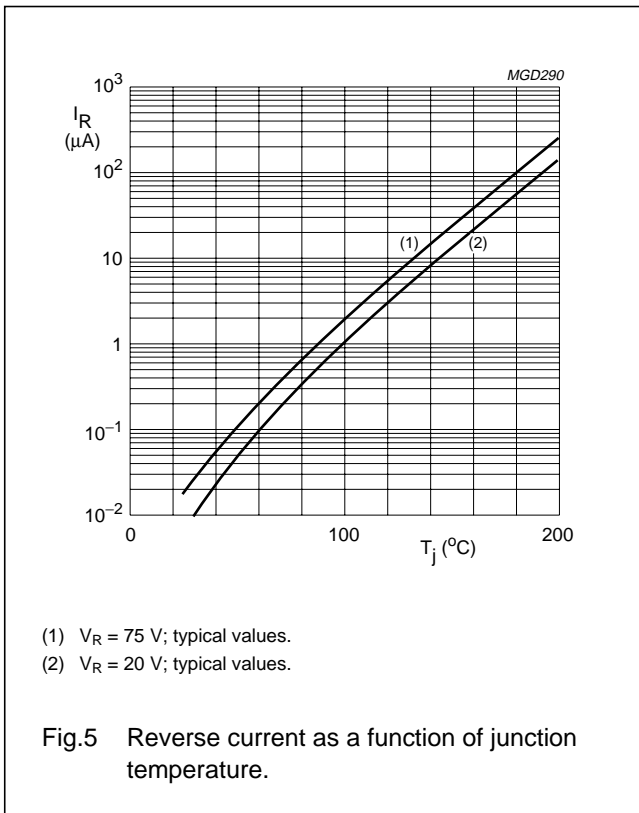
1N4148; 1N4448

GRAPHICAL DATA



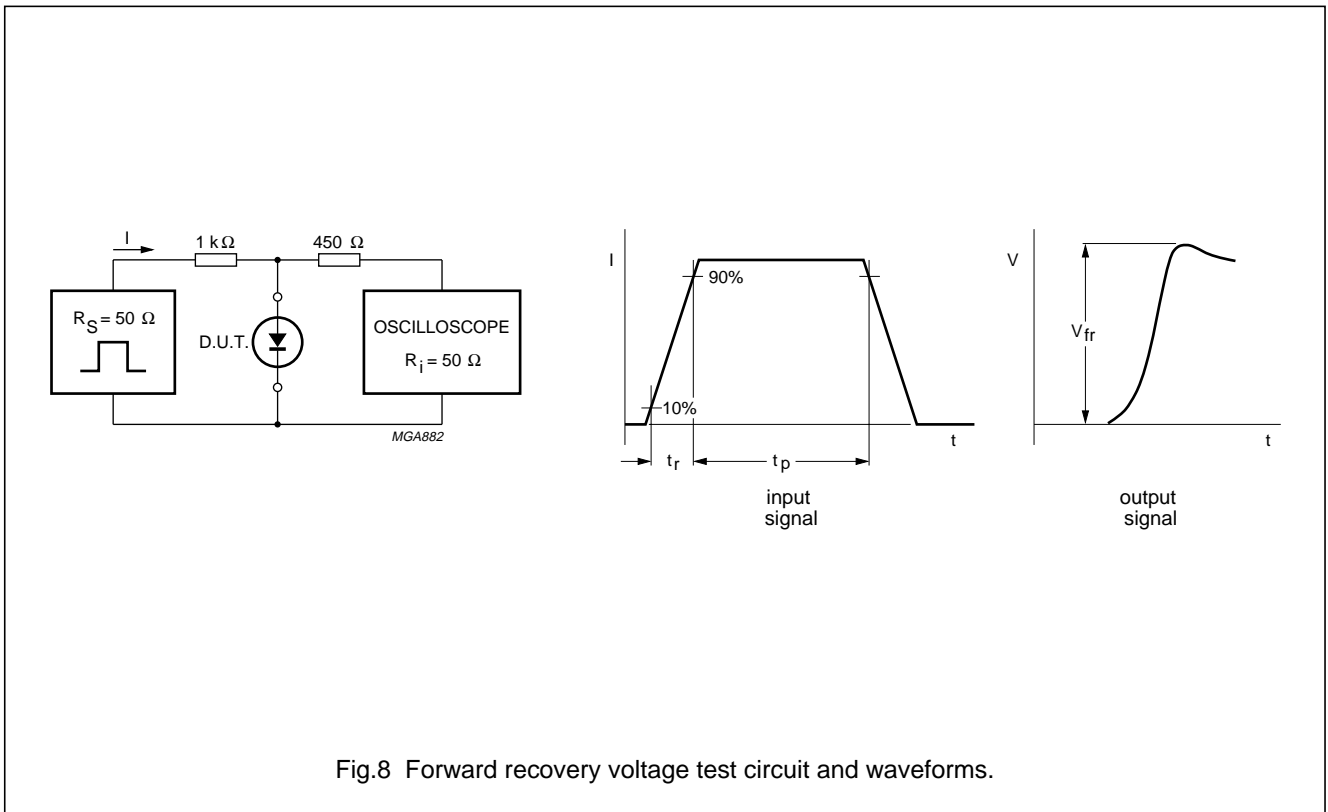
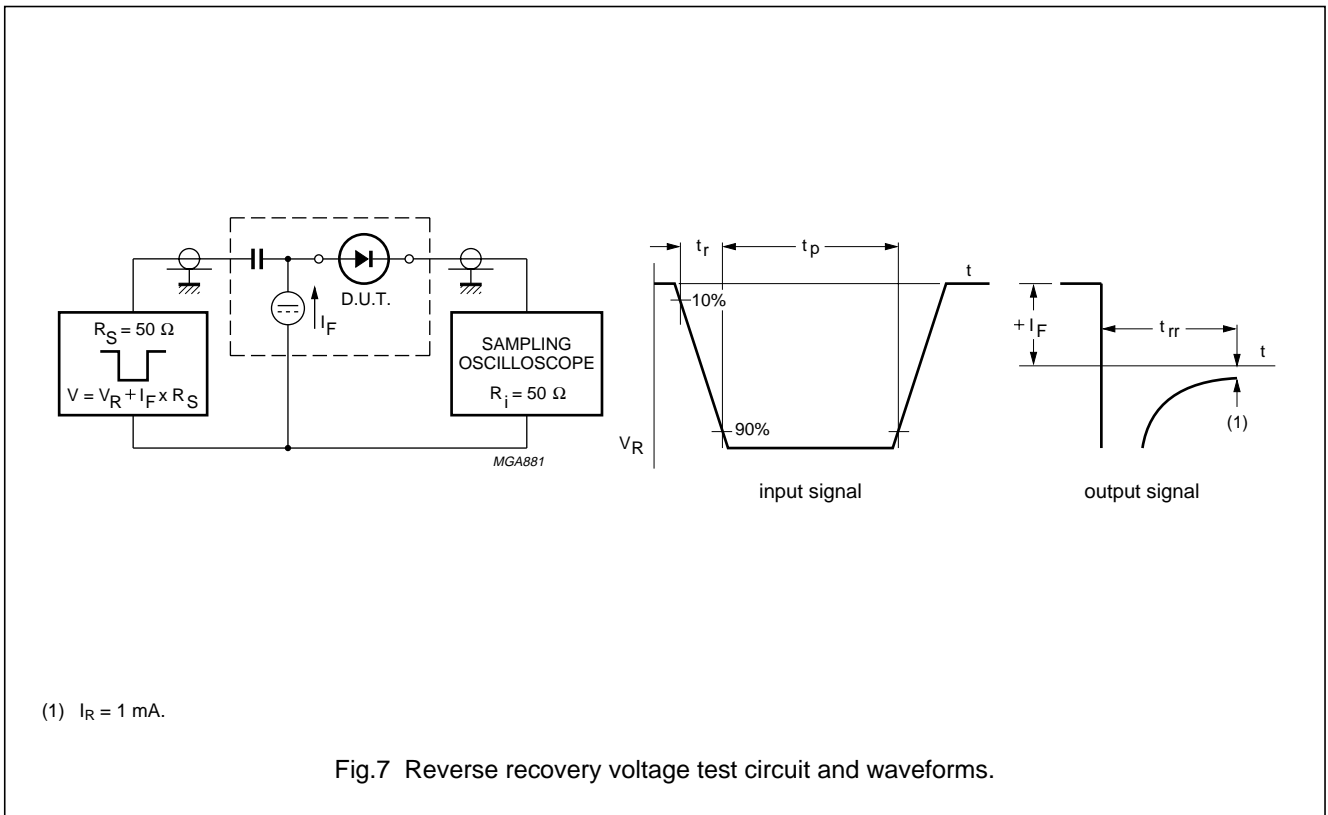
High-speed diodes

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High-speed diodes

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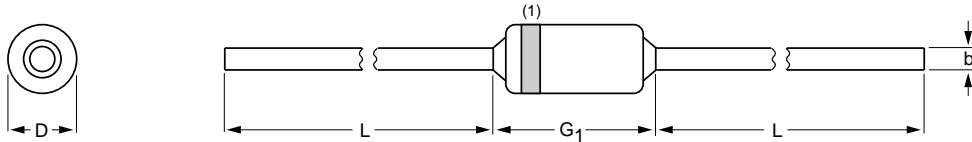
High-speed diodes

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PACKAGE OUTLINE

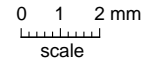
Hermetically sealed glass package; axial leaded; 2 leads

SOD27




DIMENSIONS (mm are the original dimensions)

UNIT	b max.	D max.	G <sub>1</sub> max.	L min.
mm	0.56	1.85	4.25	25.4



Note

1. The marking band indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD27	A24	DO-35	SC-40			97-06-09

## High-speed diodes

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## DATA SHEET STATUS

DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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**NOTES**

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**NOTES**

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**NOTES**

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